

Attorney Docket No. 1021269-000010



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Jong Jin Park et al.

Group Art Unit: 1756

Application No.: 10/786,592

Examiner: DABORAH CHACKO DAVIS

Filing Date:

February 26, 2004

Confirmation No.: 4344

Title: METHOD OF MAKING CARBON NANOTUBE PATTERNED FILM OR CARBON NANOTUBE

## AMENDMENT/REPLY TRANSMITTAL LETTER

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

End	losed is a reply for the above-identified patent application.				
	A Petition for Extension of Time is also enclosed.				
	Terminal Disclaimer(s) and the \$\_\\$65.00 (2814) \$\_\\$130.00 (1814) fee per Disclaimer due under 37 C.F.R. \§ 1.20(d) are also enclosed.				
	Also enclosed is/are				
	Small entity status is hereby claimed.				
	Applicant(s) requests continued examination under 37 C.F.R. § 1.114 and enclose the \$395.00 (2801) \$790.00 (1801) fee due under 37 C.F.R. § 1.17(e).				
	Applicant(s) requests that any previously unentered after final amendments <u>not</u> be entered. Continued examination is requested based on the enclosed documents identified above.				
	Applicant(s) previously submitted				
	on, for which continued examination is requested.				
	Applicant(s) requests suspension of action by the Office until at least, which does not exceed three months from the filing of this RCE, in accordance with 37 C.F.R. § 1.103(c). The required fee under 37 C.F.R. § 1.17(i) is enclosed.				
	A Request for Entry and Consideration of Submission under 37 C.F.R. § 1.129(a) (1809/2809) is also enclosed.				

Attorney Docket No. <u>1021269-000010</u> Application No. <u>10/786,592</u>

		Α	MEND	ED CLAIMS		
	No. of Claims	Highest No. of Claims Previously Paid For		Extra Claims	Rate	Additional Fee
Total Claims	16	MINUS	20 =	0	x \$50.00 (1202) =	\$ 0.00
Independent Claims	2	MINUS	3 =	0	x \$200.00 (1201) =	\$ 0.00
If Amendment adds n	nultiple depen	dent clain	ns, add	\$360.00 (1203)		
Total Claim Amendment Fee					\$ 0.00	
☐ Small Entity Sta	itus claimed -	subtract 5	60% of T	otal Claim Amend	ment Fee	\$ 0.00
TOTAL ADDITIONAL	_ CLAIM FEE	DUE FOI	R THIS A	AMENDMENT		\$ 0.00

L	A check in the amount of	is enclosed for the fee dur
	Charge	to Deposit Account No. 02-4800.
	Charge	to credit card. Form PTO-2038 is attached

The Director is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

**BUCHANAN INGERSOLL PC** 

P.O. Box 1404 Alexandria, Virginia 22313-1404 (703) 836-6620

Date: May 19, 2006

Laura L. Lee

Registration No. 48,752



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

in re Patent Application of

Jon Jin PARK et al.

Application No.: 10/786,592

Filed: February 26, 2004

For:

METHOD OF MAKING CARBON

NANOTUBE PATTERNED FILM OR ) CARBON NANOTUBE COMPOSITE)

USING CARBON NANOTUBES SURFACE-MODIFIED WITH

POLYMERIZABLE MOIETIES

Group Art Unit: 1756

Examiner: Daborah Chacko Davis

Confirmation No.: 4344

## RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In reply to the Restriction Requirement dated April 19, 2006, Applicants elect Group I, claims 1-14, for examination at this time. However, for at least the reasons set forth below, Applicants request withdrawal of the Restriction Requirement and rejoinder and examination of claims 15-16 along with claims 1-14.

Applicants submit that the claimed carbon nanotube pattern formed by the method of claim 1 is a "<u>negative</u> pattern," which is recited in claim 15 is different from a carbon nanotube pattern formed by plasma etching as set forth in the Restriction Requirement page 2, which is a "<u>positive</u> pattern."

Applicants submit that forming of a carbon nanotube pattern using plasma etching is normally performed by a process which includes the steps of (a) growing carbon nanotubes from the carbon nanotube seeds by using CVD, (b) placing the mask of a desired pattern on the surfaces of the grown carbon nanotubes and (c)

cutting the surfaces of the carbon nanotubes by plasma etching. That is, plasma

etching is a method that cuts the surfaces of the carbon nanotubes, except the part

on which pattern mask is placed by plasma, which results in a positive pattern is

formed.

On the other hand, the method of claim 1 forms a carbon nanotube pattern by

a wet chemical process and an exposing process of the coating film comprising the

carbon nanotubes to UV (please see the specification and claim 1). According to the

method of claim 1, the part exposed to UV light stays remained, so that a negative

pattern is formed.

Therefore, the product as claimed in claim 15 can not be made by the plasma

etching process as stated on page 2 of the Office Action. Further, in case of the

carbon nanotube composite, plasma etching is not in itself necessary. Therefore,

Applicants request rejoinder.

In light of the foregoing, Applicants respectfully solicit issuance of a favorable

action on the merits.

Respectfully submitted,

BUCHANAN INGERSOLL PC

Date: May 19, 2006

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